

SANYO	No.2468	2SB1296/2SD1936
		PNP/NPN Epitaxial Planar Silicon Transistors
		AF Amp Applications

Applications

- . AF power amp, medium-speed switching, small-sized motor drivers

Features

- . Large current capacity
- . Low collector to emitter saturation voltage
- . Wide ASO

(): 2SB1296

Absolute Maximum Ratings at Ta=25°C

			unit
Collector to Base Voltage	V_{CB0}	(-)15	V
Collector to Emitter Voltage	V_{CEO}	(-)15	V
Emitter to Base Voltage	V_{EBO}	(-)5	V
Collector Current	I_C	(-)0.8	A
Collector Current(Pulse)	I_{CP}	(-)3	A
Collector Dissipation	P_C	300	mW
Junction Temperature	T_J	150	°C
Storage Temperature	T_{stg}	-55 to +150	°C

Electrical Characteristics at Ta=25°C

			min	typ	max	unit
Collector Cutoff Current	I_{CB0}	$V_{CB}=(-)12V, I_E=0$			(-)100	nA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=(-)4V, I_C=0$			(-)100	nA
DC Current Gain	$h_{FE}(1)$	$V_{CE}=(-)2V, I_C=(-)50mA$	140*		(560)* 800*	
Gain-Bandwidth Product	$h_{FE}(2)$	$V_{CE}=(-)2V, I_C=(-)800mA$	80			
	f_T	$V_{CE}=(-)2V, I_C=(-)50mA$		(300)		MHz
Output Capacitance	c_{ob}	$V_{CB}=(-)10V, f=1MHz$		200		
				(15)10		pF

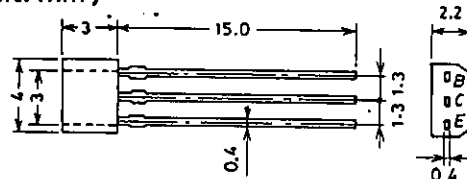
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*: The 2SB1296/2SD1936 are classified by 50mA h_{FE} as follows:

2SB1296	140	S	280	200	T	400	280	U	560
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2SD1936	140	S	280	200	T	400	280	U	560	400	V	800
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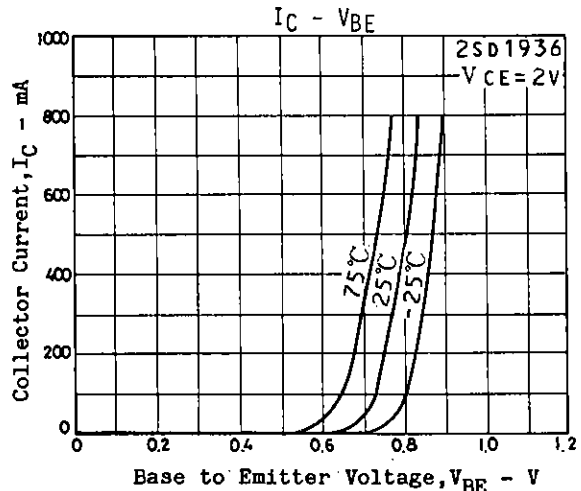
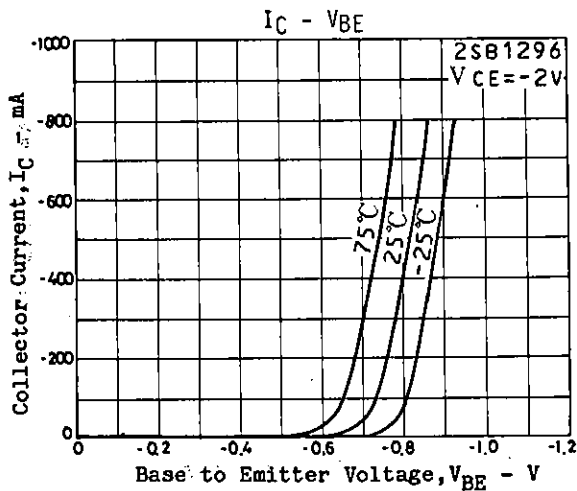
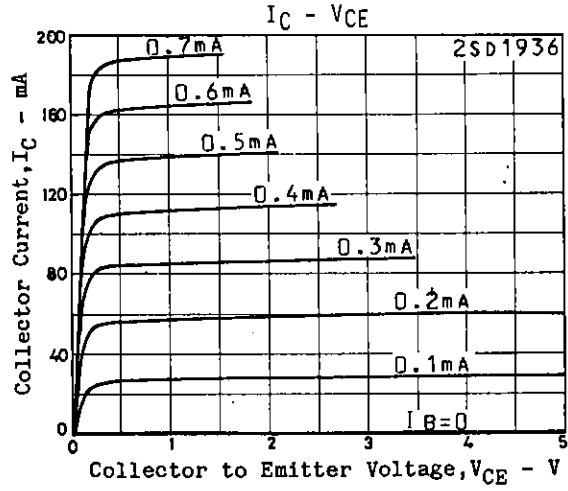
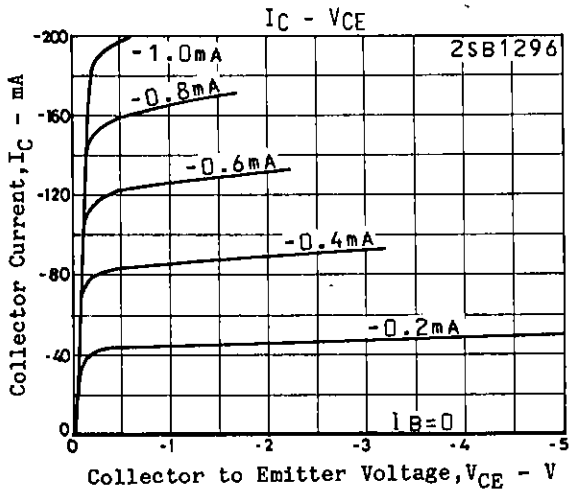
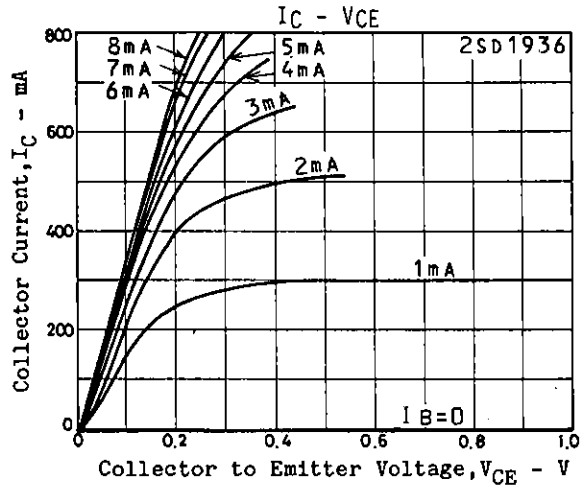
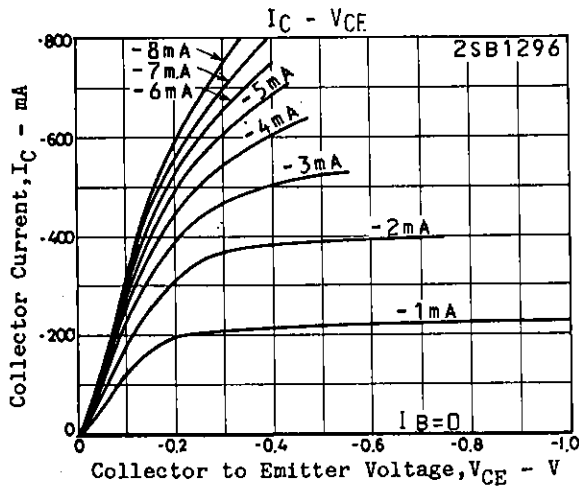
Package Dimensions 2033
(unit: mm)

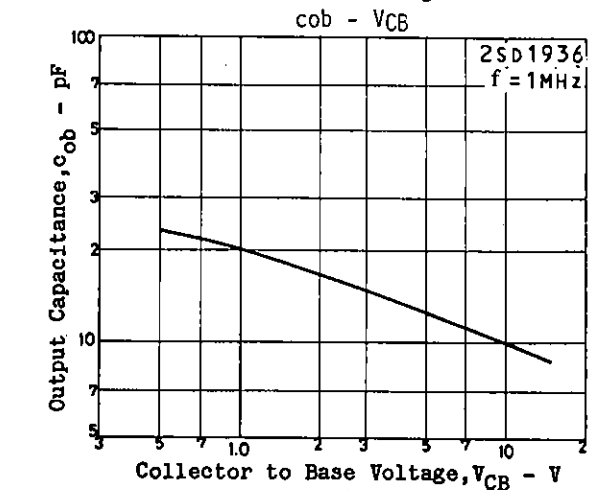
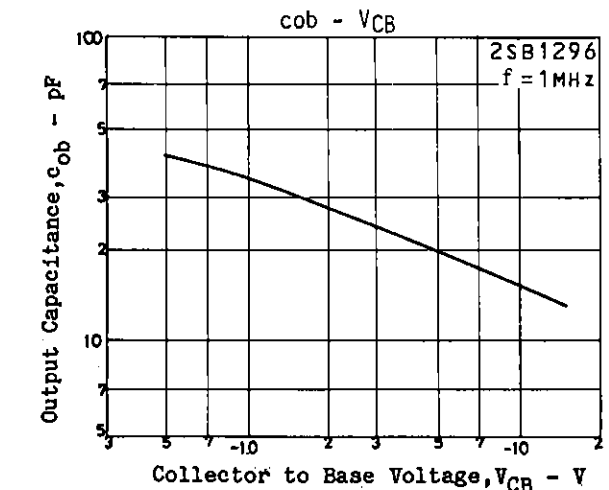
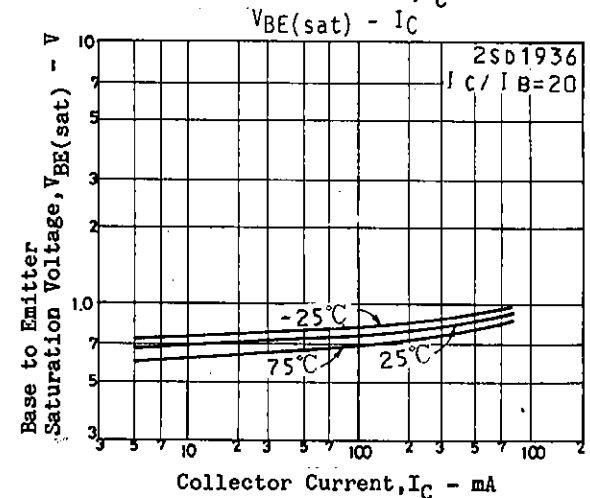
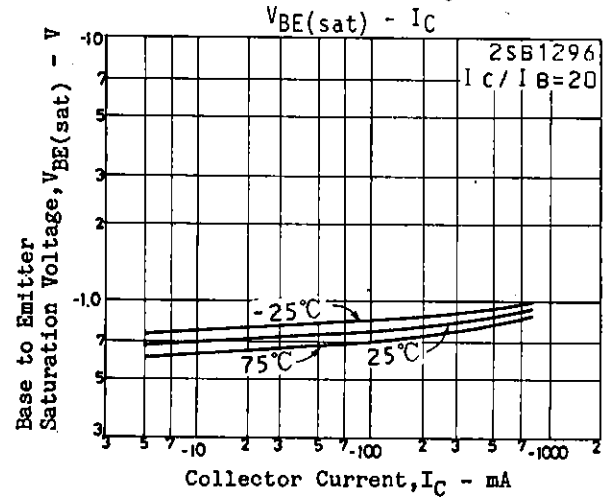
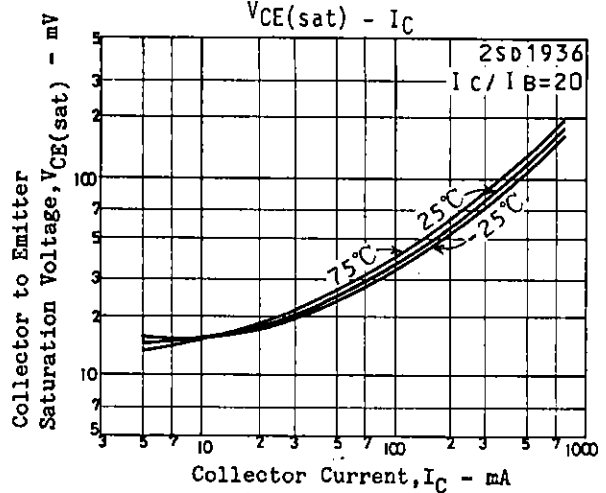
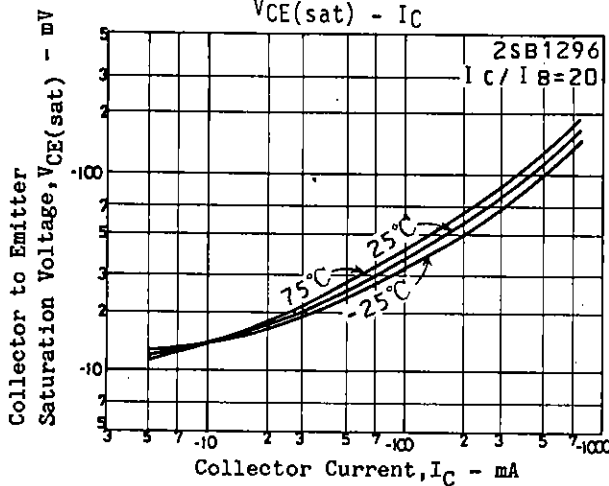
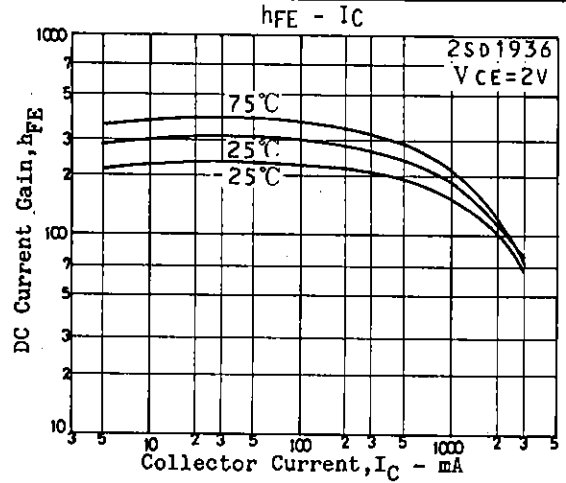
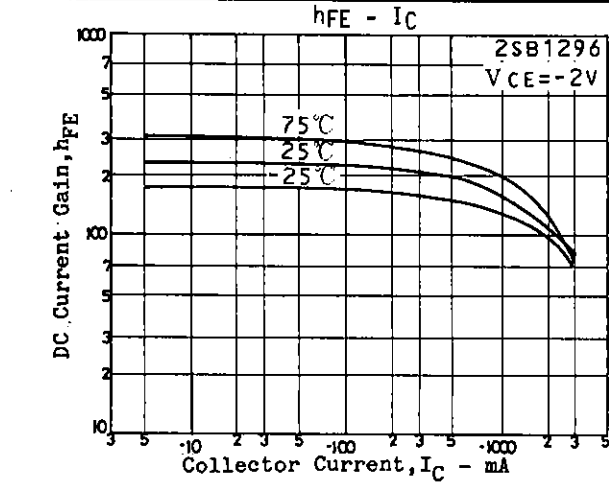


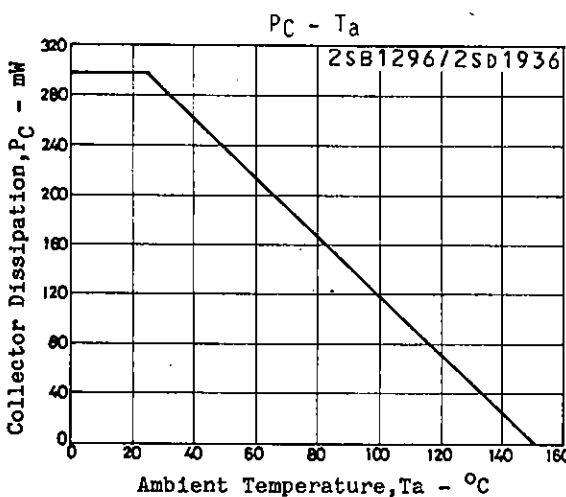
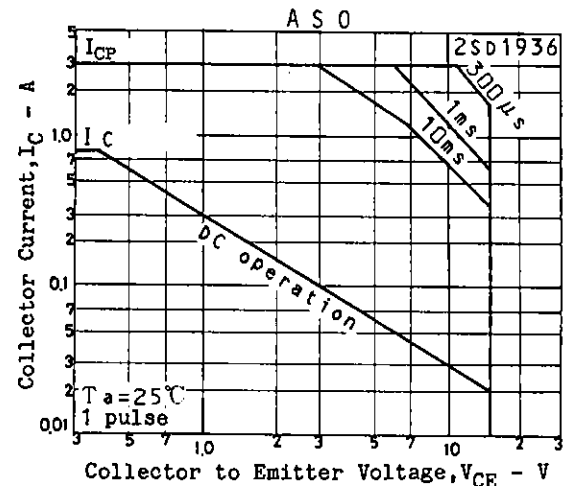
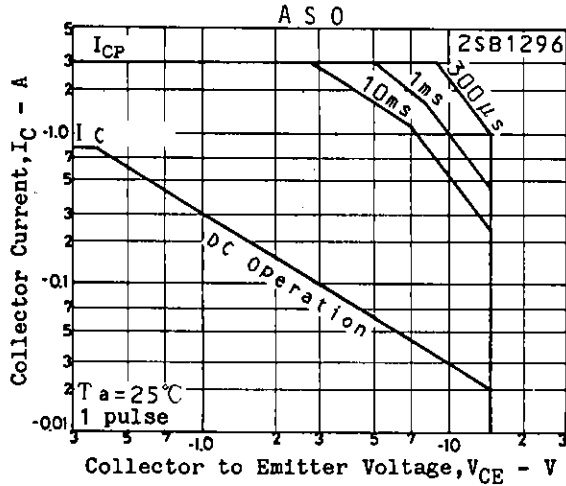
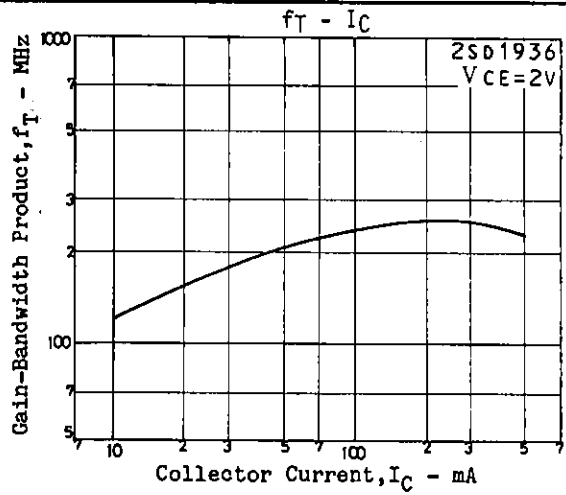
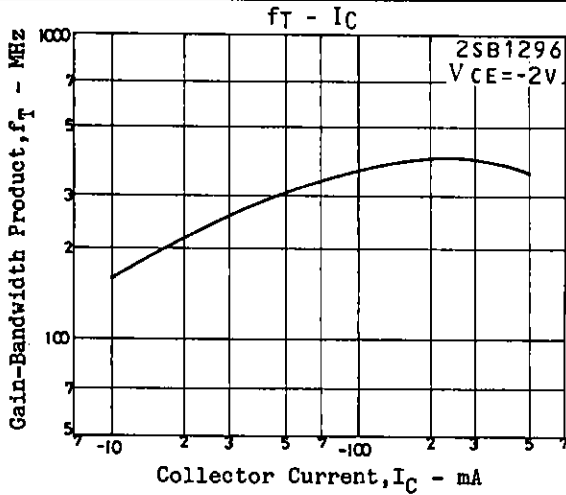
B: Base
C: Collector
E: Emitter
SANYO: SPA

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			min	typ	max	unit
C-E Saturation Voltage	$V_{CE(sat)1}$	$I_C = (-)5mA, I_B = (-)0.5mA$	(-)10	(-)25		mV
	$V_{CE(sat)2}$	$I_C = (-)400mA, I_B = (-)20mA$	(-)100	(-)200		mV
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C = (-)400mA, I_B = (-)20mA$	(-)0.9	(-)1.2		V
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C = (-)10\mu A, I_E = 0$	(-)15			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C = (-)1mA, R_{BE} = \infty$	(-)15			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E = (-)10\mu A, I_C = 0$	(-)5			V







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